www.DataSheet4U.com

Silicon NPN Power Transistors 2SC2981

DESCRIPTION

- ·With TO-3 package
- ·High voltatge
- ·High speed

APPLICATIONS

- ·For high voltatge ,high speed and power switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

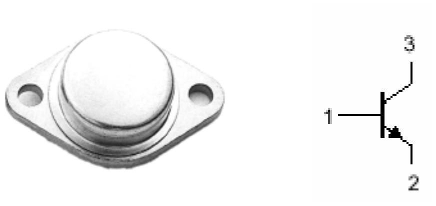

Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(T_C=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	900	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		8	A
P_C	Collector power dissipation	T_C=25℃	100	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

www.DataSheet4U.com

www.DataSheet4U.com

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=5mA ; R_{BE}=∞	800			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ; I_E=0	900			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ; I_C=0	7			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=2.5A; I_B=0.5A			1.0	V
$V_{BE(sat)}$	Base-emitter saturation voltage	I_C=2.5A; I_B=0.5A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=750V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			0.1	mA
h_{FE-1}	DC current gain	I_C=0.8A ; V_{CE}=5V	15			
h_{FE-2}	DC current gain	I_C=4A ; V_{CE}=5V	10			

www.DataSheet4U.com

www.DataSheet4U.com

PACKAGE OUTLINE

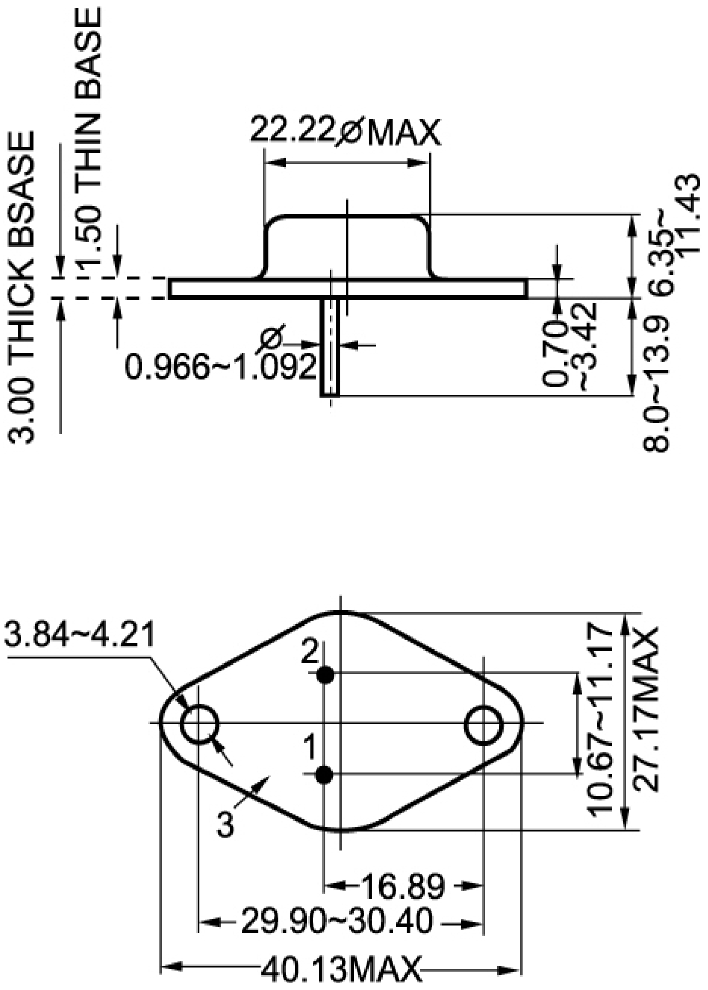

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)

www.DataSheet4U.com